

Silicon Epitaxial Base Mesa Transistor

T-33-21
T-33-11

**2SA1060 (PNP)
2SC2484 (NPN)**

TOP-3 Package (See Page 36 For Dimensions)

2SA1060 (PNP)

Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
Collector-Base Voltage	-V _{CB0}	80	V
Collector-Emitter Voltage	-V _{CEO}	80	V
Emitter-Base Voltage	-V _{EB0}	5	V
Collector Current	-I _C	5	A
Peak Collector Current	-I _{CM}	8	A
Collector Power Dissipation	P _C *	60	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

*T_c=25°C

High Power Audio Frequency Amplifier
Complementary Pair with 2SC2484

Feature

- High collector power dissipation: 60W(T_c=25°C)

**hFE Classification

hFE	100~200	60~120	40~80
Class	P	Q	R

Electrical Characteristics (Ta=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector Cutoff Current	-I _{CB0}	-V _{CB} =80V, I _E =0			50	μA
Emitter Cutoff Current	-I _{EB0}	-V _{EB} =3V, I _C =0			50	μA
DC Current Gain	hFE1	-V _{CE} =5V, -I _C =0.02A	20			
	hFE2**	-V _{CE} =5V, -I _C =1.0A	40		220	V
	hFE3	-V _{CE} =5V, -I _C =3A	20			
Base Emitter Voltage	-V _{BE}	-V _{CE} =5V, -I _C =3A			1.8	V
Collector-Emitter Saturation Voltage	-V _{CE(sat)}	-I _C =3A, -I _B =0.3			2.0	V
Gain Bandwidth Product	f _T	-V _{CE} =5V, -I _C =0.5A		20		MHz

2SC2484 (NPN)

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High Power Audio Frequency Amplifier
Complementary Pair with 2SA1060

Feature:

- High collector power dissipation: 60W(T_c=25°C)

**hFE Classification

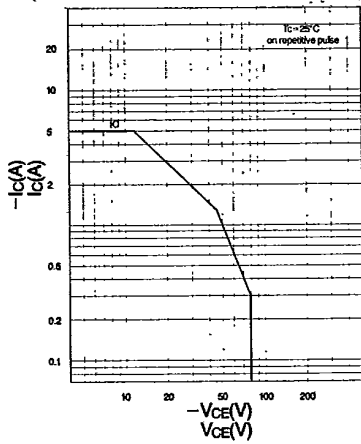
hFE	100~200	60~120	40~80
Class	P	Q	R

Electrical Characteristics (Ta=25°C)

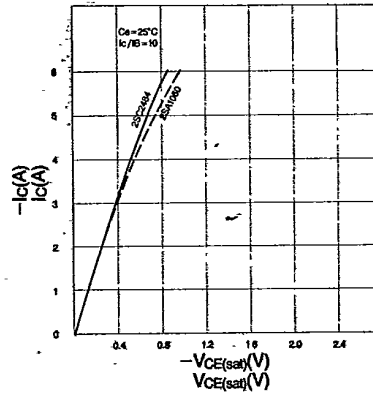
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Emitter Cutoff Current	I _{EB0}	V _{EB} =3V, I _C =0			50	μA
DC Current Gain	hFE1	V _{CE} =5V, I _C =0.02A	20			
	hFE2**	V _{CE} =5V, I _C =1.0A	40		220	V
	hFE3	V _{CE} =5V, I _C =3A	20			
Base Emitter Voltage	V _{BE}	V _{CE} =5V, I _C =3A			1.8	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =3A, I _B =0.3A			2.0	V
Gain Bandwidth Product	f _T	V _{CE} =5V, I _C =0.5A		20		MHz

Typical Characteristics

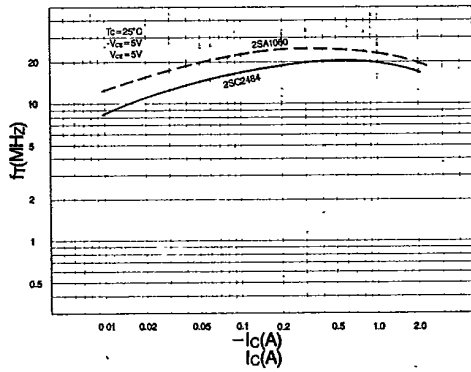
Area of Safe Operation (ASO) ($T_c = 25^\circ\text{C}$)



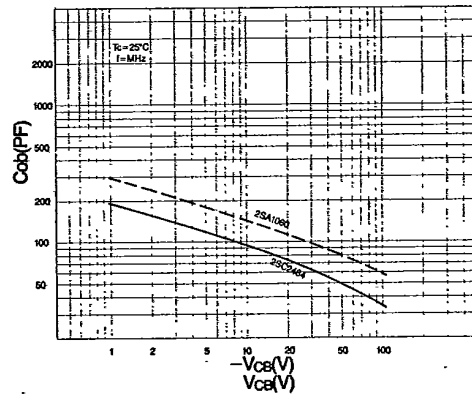
$V_{ce(sat)}$ vs. I_c characteristics



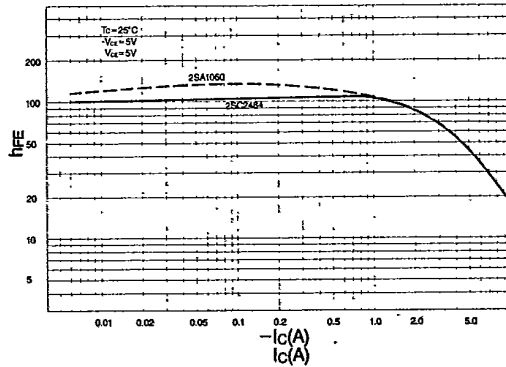
f_T vs. I_c characteristics



C_{ob} vs. V_{cb} characteristics



h_{FE} vs I_c characteristics



V_{BE} vs. I_c characteristics

